Features

- Wide Frequency Range: 20 - 45 GHz
- High Gain: 24.5 dB @ 39 GHz
- P1dB: 23.5 dBm @ 39 GHz
- Output IP3: 30 dBm
- Integrated Power Detector
- Bare Die
- RoHS* Compliant

Applications

- ISM/MM

Description

The MAAM-011277-DIE is a 4-stage, 0.25 W power amplifier 2.5 x 1.15 mm MMIC die. This power amplifier operates from 20 to 45 GHz and provides 22 dB of linear gain, 0.25 W at P1dB compression, and 17% efficiency (P3) while biased at 5 V.

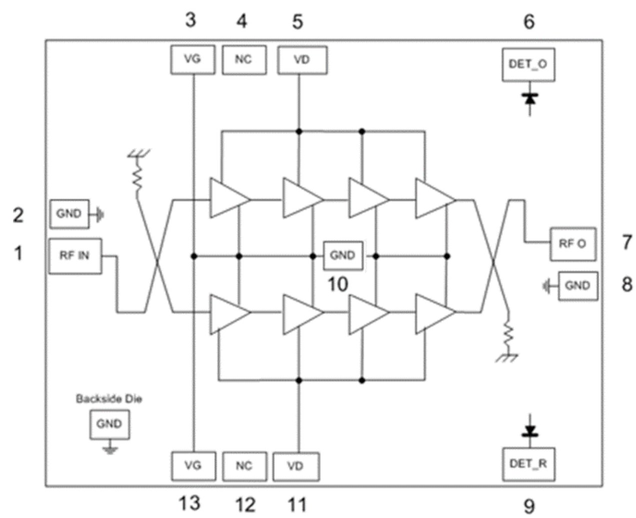
This device can be used as a driver amplifier ideally suited for various operational band in between 20 GHz and 45 GHz.

This product is fabricated using a GaAs pHEMT process which features full passivation for enhanced reliability.

Ordering Information

Part Number	Package
MAAM-011277-DIE	Bare Die

Functional Schematic



Pin Configuration[1]

Pin #	Pin Name	Description
1	IN	RF Input
2, 8	GND	Ground
3, 13	VG	Gate Voltage
4, 10, 12	N/C	Not Connected
5, 11	VD	Drain Voltage
6	VDET_O	Detector Voltage
9	VDET_R	Detector Reference
7	OUT	RF Output

1. Backside of die must be connected to RF, DC and thermal ground.

* Restrictions on Hazardous Substances, compliant to current RoHS EU directive.

Electrical Specifications: Freq. = 20 - 45 GHz, T_A = +25°C, V_D = 5 V, I_{DSQ} = 0.3 A, Z_0 = 50 Ω

Parameter	Test Conditions	Units	Min.	Typ.	Max.
Gain	P_{IN} = -10 dBm 20 GHz 30 GHz 39 GHz 45 GHz	dB	21.0 18.5 21.5 —	24.0 20.0 24.5 18.5	—
Input Return loss	—	dB	—	15	—
Output Return Loss	—	dB	—	15	—
P1dB	20 GHz 30 GHz 39 GHz 45 GHz	dBm	21.5 21.0 22.5 —	23.0 22.5 23.5 22.0	—
P3dB	—	dBm	—	25	—
OIP3	P_{OUT}/Tone = 18 dBm, Δf = 10 MHz	dBm	—	30	—
Drain Voltage	—	V	—	5	—
Drain Current @ P1dB	—	mA	—	400	500
Power Added Efficiency	P3dB	%	—	17	—

Maximum Operating Ratings

Parameter	Rating
Input Power	P_{IN} ≤ 3dB Compression
Junction Temperature[2,3]	+160°C
Operating Temperature	-40°C to +85°C

2. Operating at nominal conditions with junction temperature ≤ +160°C will ensure MTTF > 1 x 10^6 hours.
3. Junction Temperature (T_J) = T_C + Θ_{JC} * [(V * I) - (P_{OUT} - P_{IN})]. Typical thermal resistance (Θ_{JC}) = 16.7°C/W
   a) For T_C = +25°C
      T_J = 56.2°C @ 5 V, 443 mA, P_{OUT} = 25.4 dBm, P_{IN} = 4 dBm
   b) For T_C = +85°C
      T_J = 117.1°C @ 5 V, 434 mA, P_{OUT} = 24.0 dBm, P_{IN} = 8 dBm

Handling Procedures
Please observe the following precautions to avoid damage:

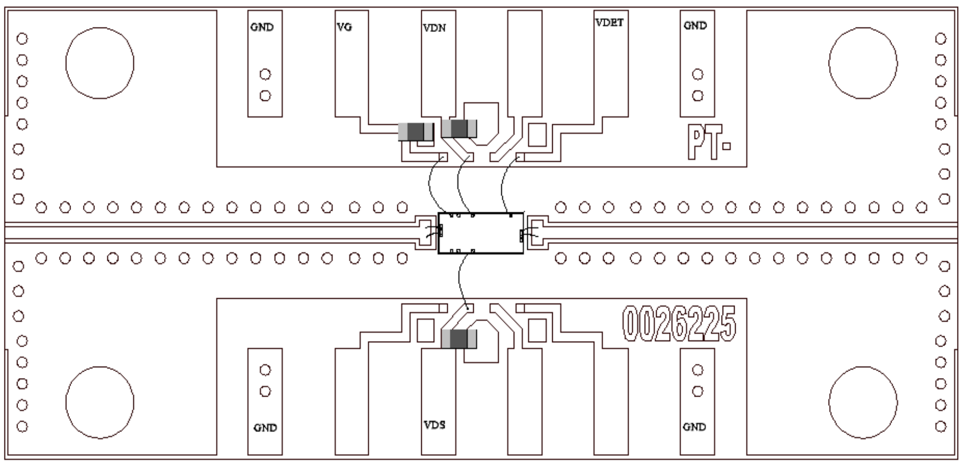
Static Sensitivity
These electronics devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these 250 V HBM Class 1A devices.

Absolute Maximum Ratings[4,5]

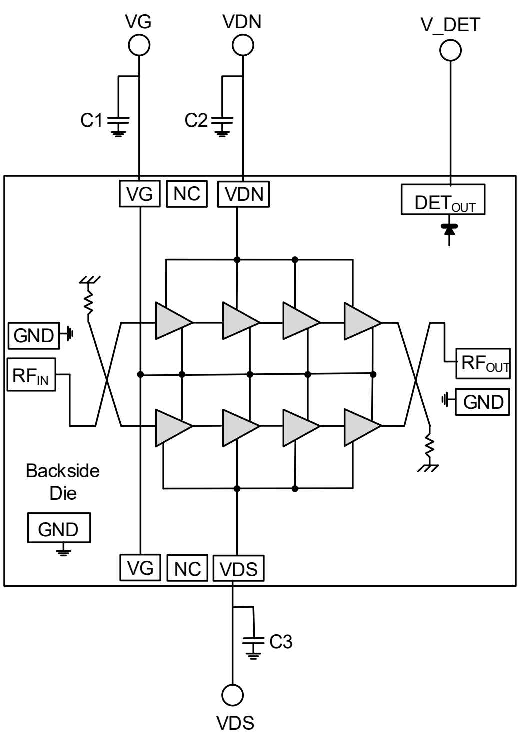
Parameter	Absolute Maximum
Input Power	23 dBm
Drain Voltage	6 V
Gate Voltage	-3 to 0 V
Junction Temperature[6]	+175°C
Storage Temperature	-65°C to +125°C

4. Exceeding any one or combination of these limits may cause permanent damage to this device.
5. MACOM does not recommend sustained operation near these survivability limits.
6. Junction temperature directly effects device MTTF. Junction temperature should be kept as low as possible to maximize lifetime.

Sample Board Layout



Application Schematic



Parts List

Part	Value	Case Style
C1 - C3	1 µF	0402

Sample Board Thru Loss

Refer to the plot on page 9 for sample board thru loss.

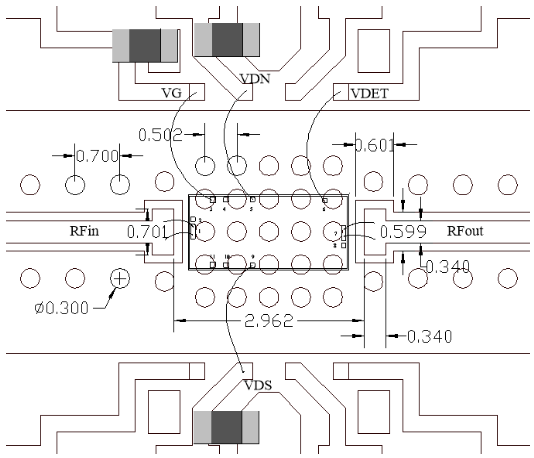
Sample Board Material Specifications

Top Layer: 1/2 oz Copper Cladding, 0.0175 mm thickness
Dielectric Layer: Rogers RO4003C 0.203 mm thickness
Bottom Layer: 1/2 oz Copper Cladding, 0.0175 mm thickness
Finished overall thickness: 0.238 mm

Recommended Bonding Diagram and PCB Details:

For optimum performance, RF input and output transmission lines require open stubs on the application board for bonding wire inductance compensation. The physical length for the 1 mil diameter gold wire is approximately 350 µm each for the two wire connection.

Use copper filled and plated over vias for the thermal, DC and RF ground vias.



Units are in mm.

Biasing Conditions

Recommended biasing conditions are V_D = 5 V, I_{DQ} = 300 mA (controlled with V_G). The drain bias voltage range is 4 to 6 V, and the quiescent drain current biasing range is 250 to 350 mA.

V_G pins 3 and 11 are internally connected; therefore, interconnection is not required. Muting can be accomplished by setting the V_G to the pinched off voltage (V_G = -2 V).

V_D bias must be applied to V_{DN} and V_{DS} (north and south). North V_D supplies and south V_D supplies are not connected internally.

Operating the MAAM-011277-DIE

Turn-on

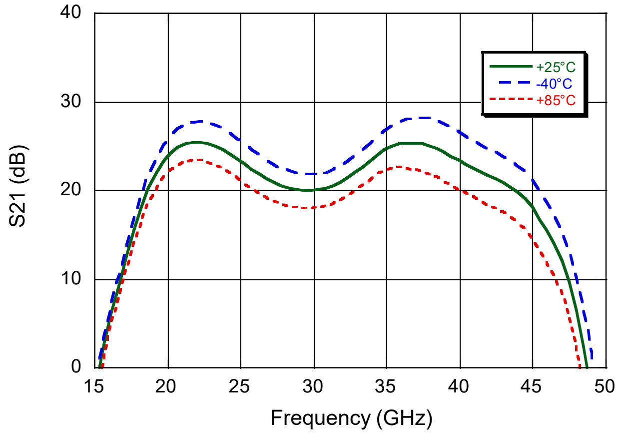
1. Apply V_G (-1.5 V).
2. Apply V_D (5.0 V typical).
3. Set I_{DQ} by adjusting V_G more positive (typically -0.9 to -1.0 V for I_{DQ} = 300 mA).
4. Apply RF_{IN} signal.

Turn-off

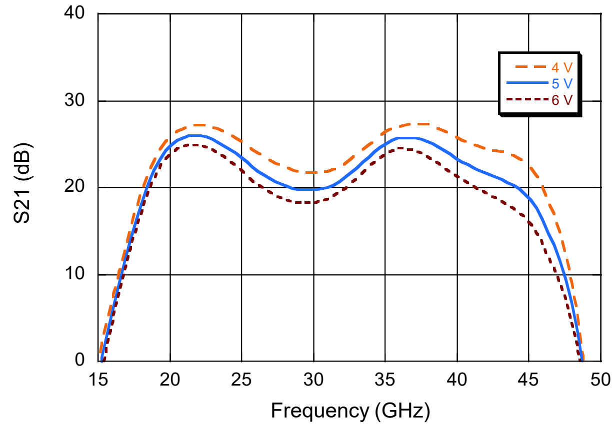
1. Remove RF_{IN} signal.
2. Decrease V_G to -1.5 V.
3. Decrease V_D to 0 V.

Typical Performance Curves: V_D = 5 V, I_{DSQ} = 300 mA

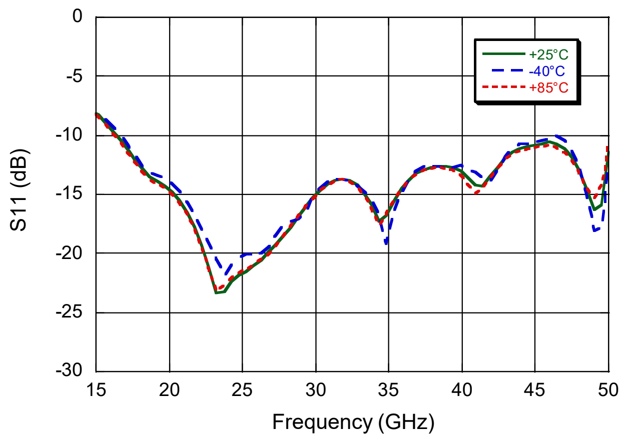
Small Signal Gain vs. Frequency



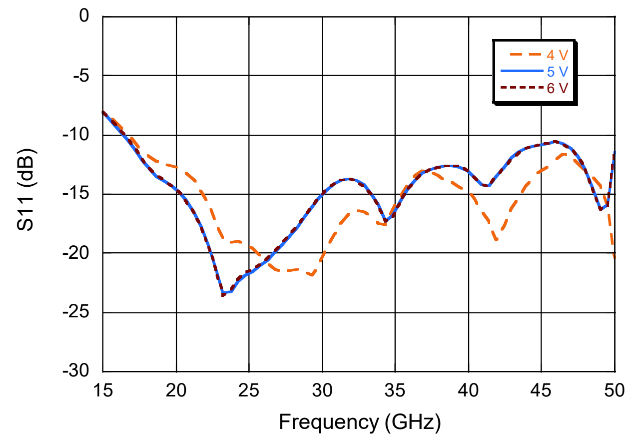
Small Signal Gain vs. Frequency



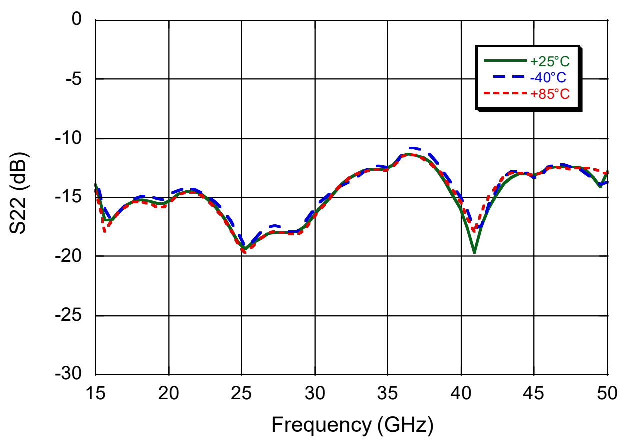
Input Return Loss vs. Frequency



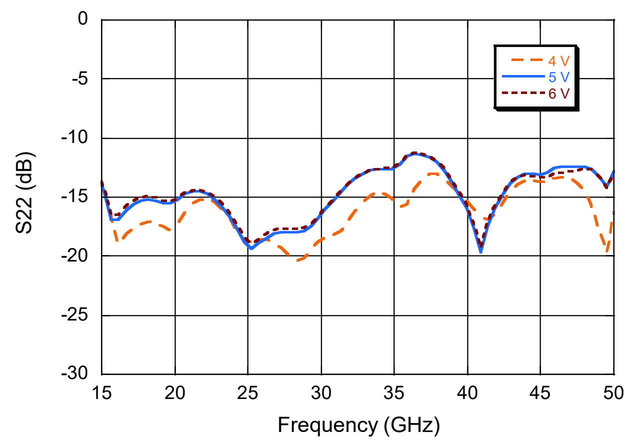
Input Return Loss vs. Frequency



Output Return Loss vs. Frequency

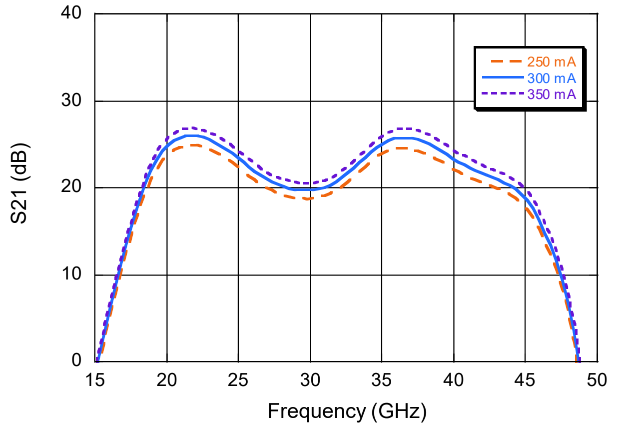


Output Return Loss vs. Frequency

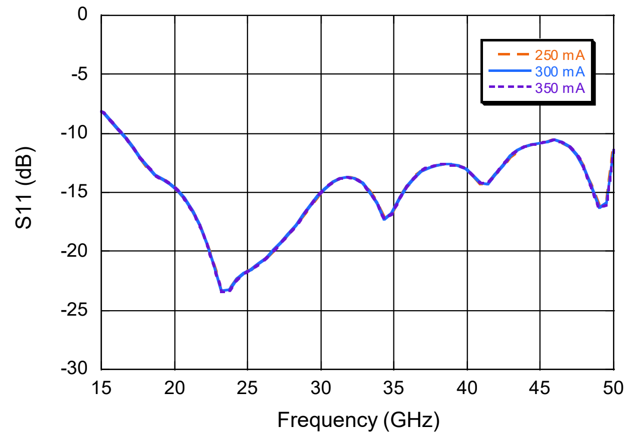


Typical Performance Curves: V_D = 5 V

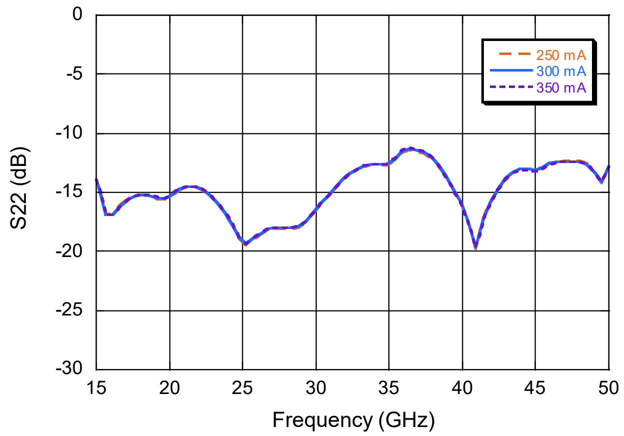
Small Signal Gain vs. Frequency



Input Return Loss vs. Frequency

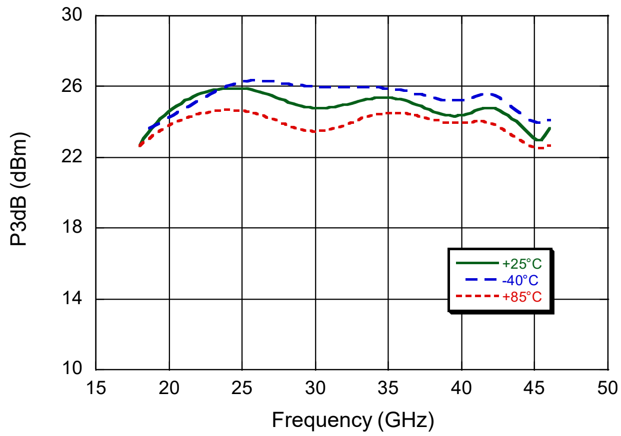


Output Return Loss vs. Frequency

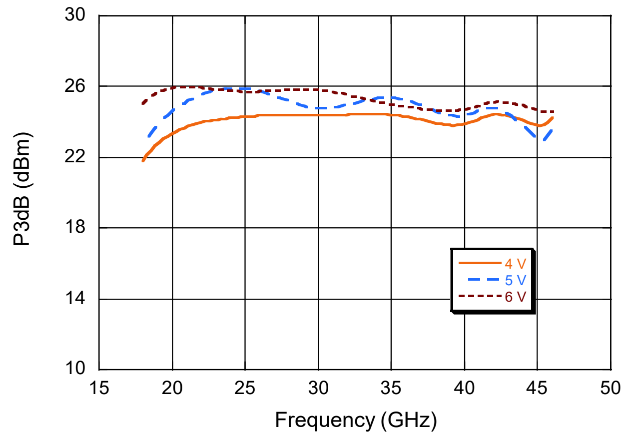


Typical Performance Curves: V_D = 5 V, I_{DSQ} = 300 mA

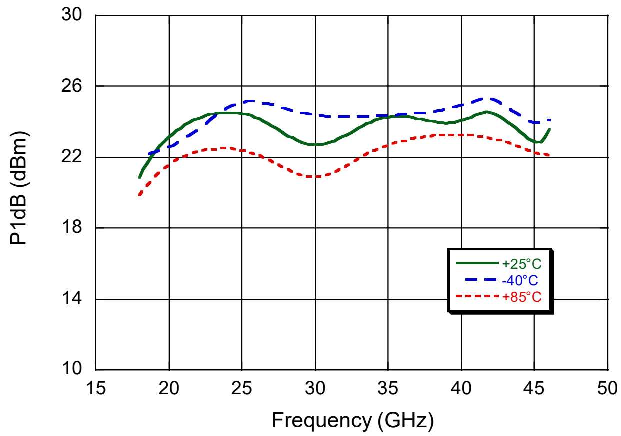
P3dB vs. Frequency



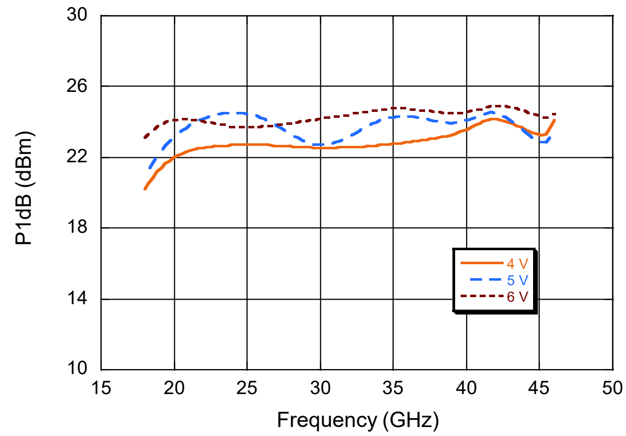
P3dB vs. Frequency



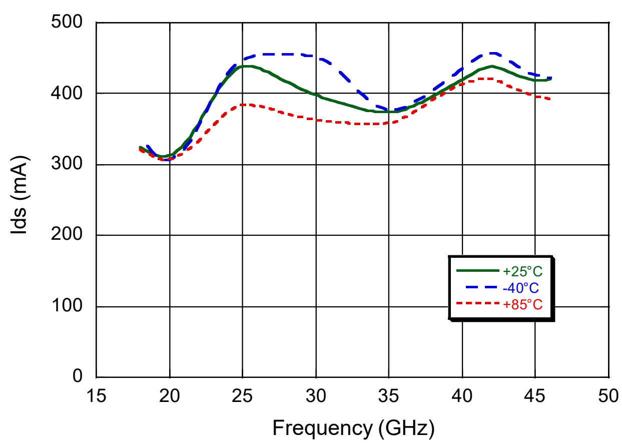
P1dB vs. Frequency



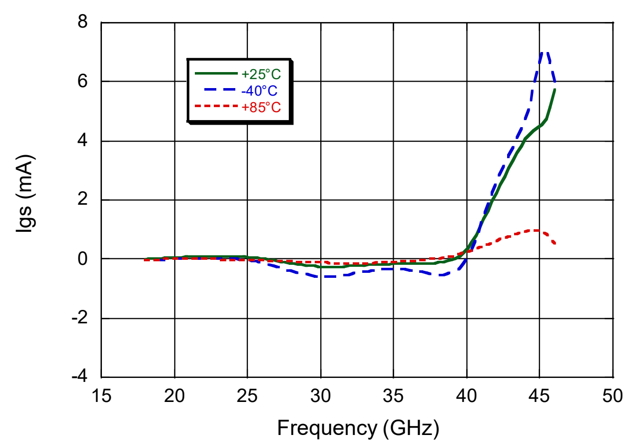
P1dB vs. Frequency



Ids vs. Frequency @ P3dB

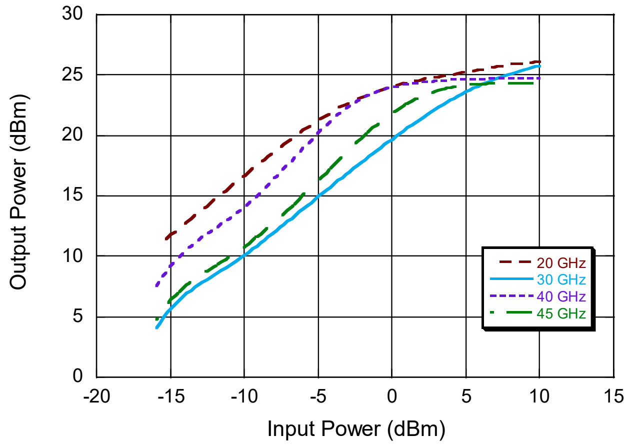


Igs vs. Frequency @ P3dB

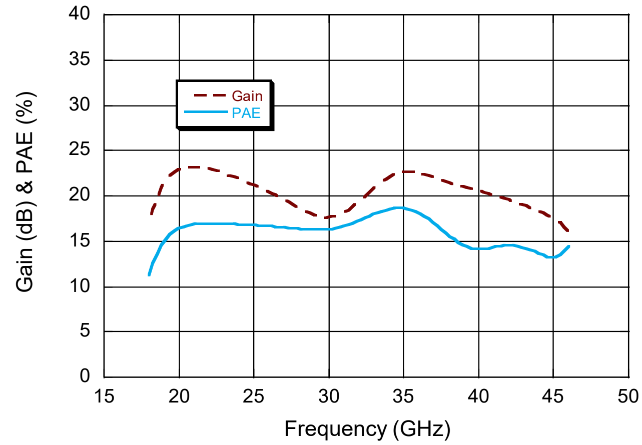


Typical Performance Curves: V_D = 5 V, I_{DSQ} = 300 mA

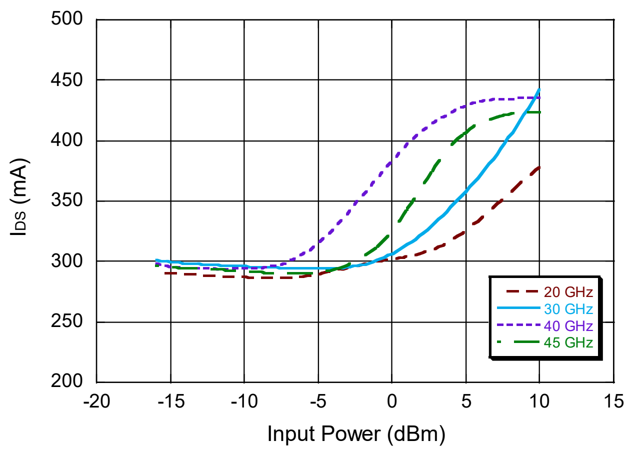
Output Power vs. Input Power



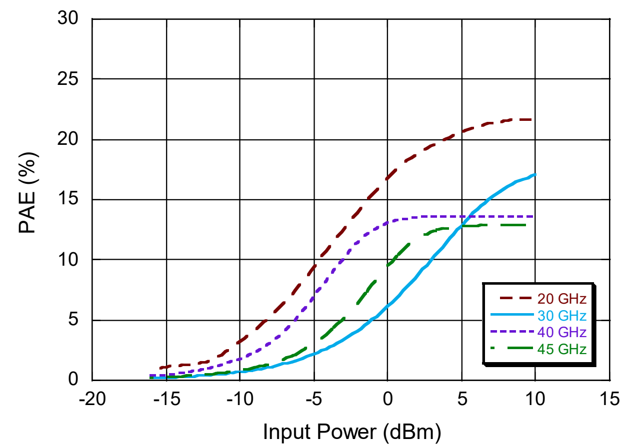
Gain and PAE @ P3dB vs. Frequency



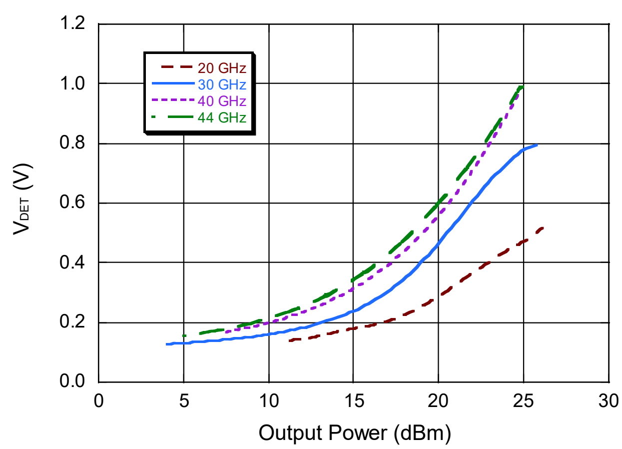
Drain Current vs. Input Power



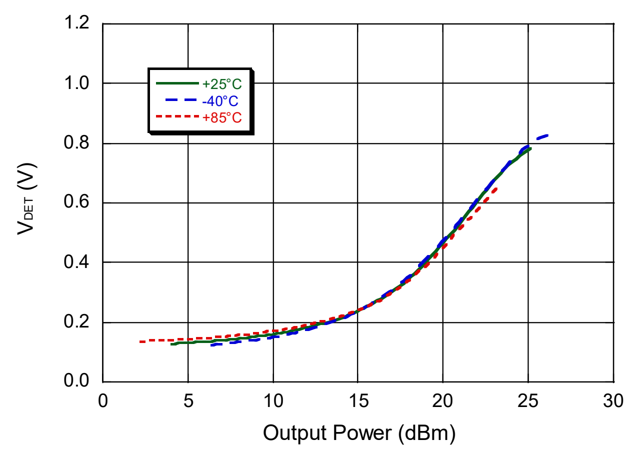
PAE vs. Input Power



Detector Voltage vs. Output Power

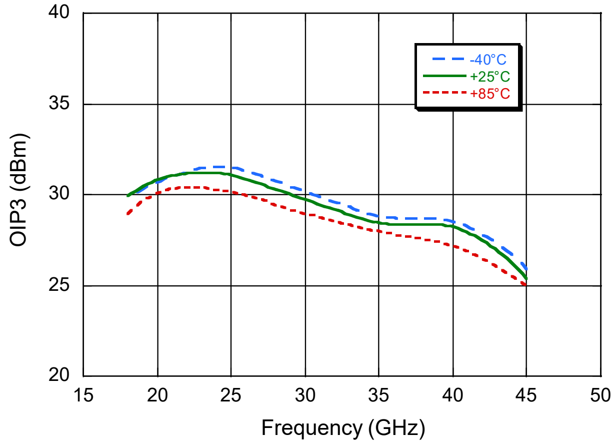


Detector Voltage vs. Output Power @ 30 GHz

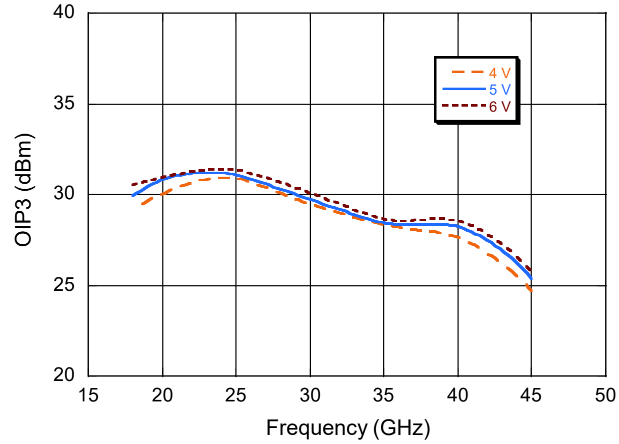


Typical Performance Curves: V_D = 5 V, I_{DSQ} = 300 mA

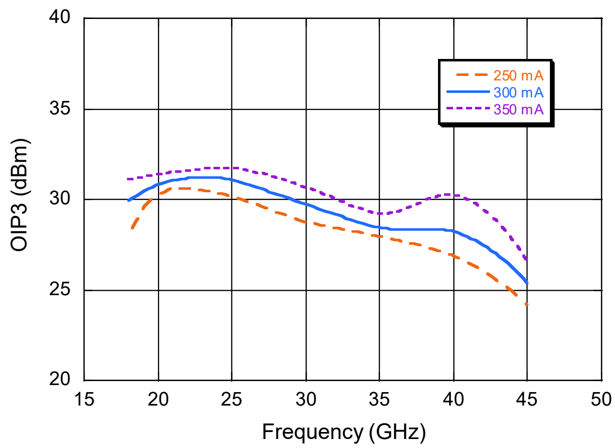
Output IP3 vs. Frequency @ Pout = 18 dBm / Tone



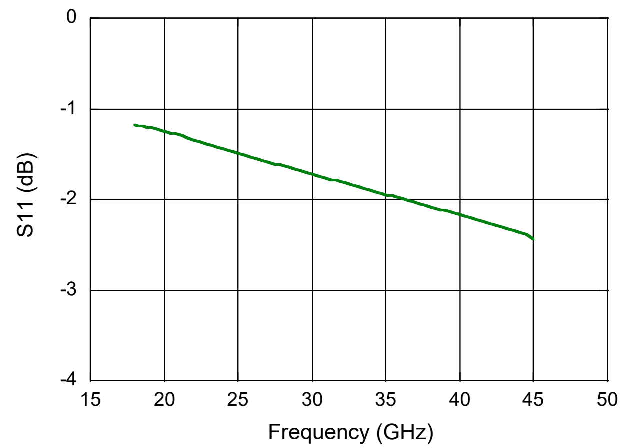
Output IP3 vs. Frequency @ Pout = 18 dBm / Tone



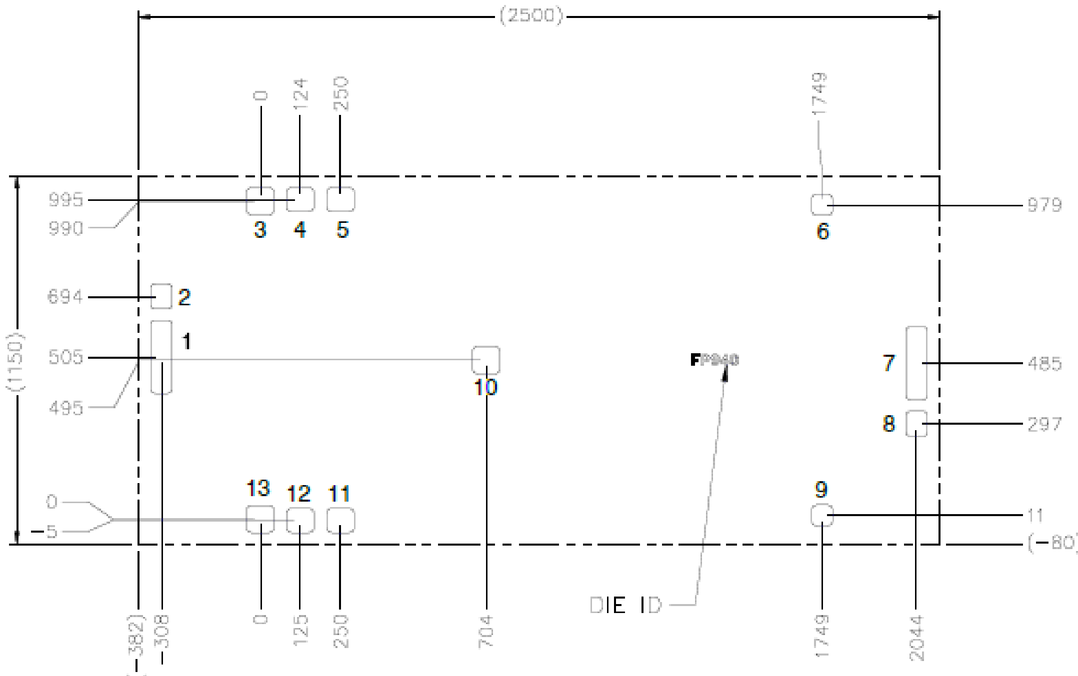
Output IP3 vs. Frequency @ Pout = 18 dBm / Tone



Sample Board Thru Losses
Includes Two 2.4 mm Connectors



Die Dimensions



Units are in micro meters with a tolerance of ±5 µm, except for die exterior dimensions which are street-center-to-street-center – nominal saw or laser kerf is ~25 µm each dimension. Pads and backside metal are gold. Die thickness is 100 ± 10 µm.

Pad Dimensions (µm)

Pad #	X	Y
1, 7	68	228
2, 8	68	78
3, 10, 13	85	85
4, 5, 11, 12	75	85
6, 9	65	65